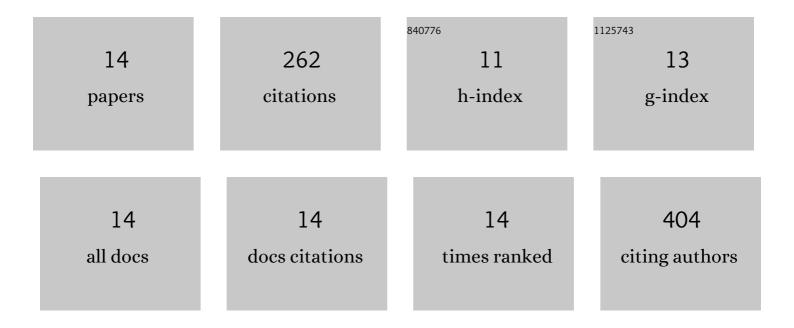
C Thomidis

List of Publications by Year in descending order

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СТномірія

| # | Article | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Phosphorous Diffusion in N2+-Implanted Germanium during Flash Lamp Annealing: Influence of Nitrogen on Ge Substrate Damage and Capping Layer Engineering. ECS Journal of Solid State Science and Technology, 2017, 6, P418-P428. | 1.8 | 5 |
| 2 | Strong Diffusion Suppression of Low Energy-Implanted Phosphorous in Germanium by N2 Co-Implantation. ECS Solid State Letters, 2015, 4, P47-P50. | 1.4 | 11 |
| 3 | Molecular beam epitaxy growth of AlGaN quantum wells on 6H-SiC substrates with high internal quantum efficiency. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 02B119. | 1.2 | 22 |
| 4 | InGaN-based LEDs grown by plasma-assisted MBE on (0001) sapphire with GaN QDs in the nucleation layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2309-2311. | 0.8 | 7 |
| 5 | Growth and properties of nearâ€UV light emitting diodes based on InN/GaN quantum wells. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1070-1073. | 1.8 | 57 |
| 6 | Growth of Illâ€nitride quantum dots and their applications to blueâ€green LEDs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2560-2565. | 1.8 | 28 |
| 7 | InGaN-based LEDs grown by plasma-assisted MBE on (0001) sapphire with GaN QDs in the nucleation layer. , 2008, 5, 2309. | | 1 |
| 8 | Growth of InN films by RF plasma-assisted MBE and cluster beam epitaxy. Journal of Crystal Growth, 2006, 288, 254-260. | 1.5 | 15 |
| 9 | High power ultraviolet light emitting diodes based on GaNâ^•AlGaN quantum wells produced by molecular beam epitaxy. Journal of Applied Physics, 2006, 100, 104506. | 2.5 | 21 |
| 10 | Enhanced internal quantum efficiency and light extraction efficiency from textured GaNâ^•AlGaN quantum wells grown by molecular beam epitaxy. Journal of Applied Physics, 2006, 99, 064904. | 2.5 | 22 |
| 11 | Growth and silicon doping of AlGaN films in the entire alloy composition by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2220-2223. | 0.8 | 18 |
| 12 | Ultraviolet electroabsorption modulator based on AlGaNâ^•GaN multiple quantum wells. Journal of Applied Physics, 2005, 97, 123515. | 2.5 | 22 |
| 13 | Well width dependence of disorder effects on the optical properties of AlGaNâ^•GaN quantum wells. Applied Physics Letters, 2004, 85, 3068-3070. | 3.3 | 13 |
| 14 | Investigation of excitons in AlGaN/GaN multiple quantum wells by lateral photocurrent and photoluminescence spectroscopies. Journal of Applied Physics, 2004, 95, 3495-3502. | 2.5 | 20 |